

# RJH60D5DPK

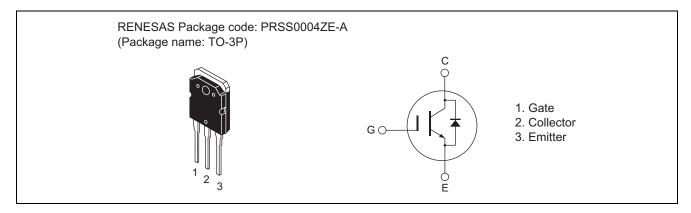
Silicon N Channel IGBT Application: Inverter

REJ03G1846-0100 Rev.1.00 Oct 14, 2009

## **Features**

- High breakdown-voltage
- Low on-voltage
- Built-in diode

## **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item		Symbol	Ratings	Unit	
Collector to emitter voltage / diode reverse voltage		V <sub>CES</sub> / V <sub>R</sub>	600	V	
Gate to emitter voltage		$V_{GES}$	±30	V	
Collector current	Tc = 25°C	Ic	60	Α	
	Tc = 100°C	Ic	30	Α	
Collector peak current		ic(peak) Note1	120	Α	
Collector to emitter diode forward current		I <sub>DF</sub>	30	Α	
Collector to emitter diode forward peak current		i <sub>DF</sub> (peak) Note1	120	Α	
Collector dissipation		P <sub>C</sub> Note2	200	W	
Junction to case thermal impedance		θj-c <sup>Note2</sup>	0.63	°C/W	
Junction temperature		Tj	150	°C	
Storage temperature		Tstg	-55 to +150	°C	

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

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## **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

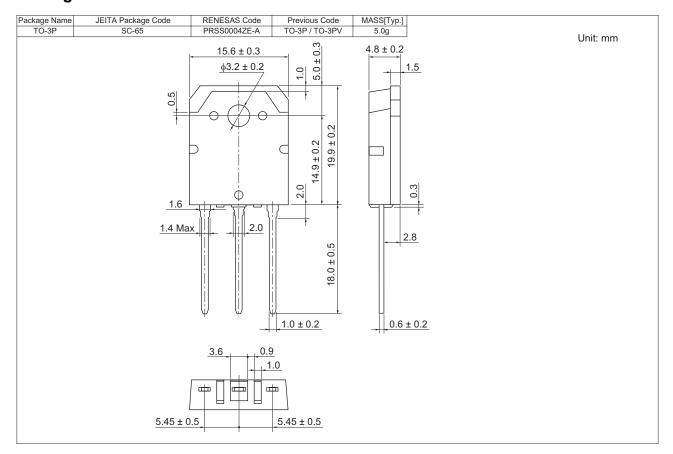
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current / Diode reverse current	I <sub>CES</sub> / I <sub>R</sub>	_	_	100	μА	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0
Gate to emitter leak current	I <sub>GES</sub>	_	_	±1	μА	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4.0	_	6.0	V	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 1 mA
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	1.6	2.2	V	I <sub>C</sub> = 30 A, V <sub>GE</sub> = 15 V <sup>Note3</sup>
	V <sub>CE(sat)</sub>	_	1.8	_	V	$I_C = 60 \text{ A}, V_{GE} = 15 \text{ V}^{\text{Note3}}$
Input capacitance	Cies	_	1900	_	pF	V <sub>CE</sub> = 25 V
Output capacitance	Coes	_	130	_	pF	V <sub>GE</sub> = 0
Reveres transfer capacitance	Cres	_	60	_	pF	f = 1 MHz
Total gate charge	Qg	_	79	<u> </u>	nC	V <sub>GE</sub> = 15 V
Gate to emitter charge	Qge	_	11	_	nC	V <sub>CE</sub> = 300 V
Gate to collector charge	Qgc		33	_	nC	I <sub>C</sub> = 30 A
Switching time	t <sub>d(on)</sub>		45	_	ns	I <sub>C</sub> = 30 A
	t <sub>r</sub>		65	_	ns	$R_L = 10 \Omega$
	t <sub>d(off)</sub>	_	125	_	ns	V <sub>GE</sub> = 15 V
	t <sub>f</sub>	_	75	_	ns	$Rg = 5 \Omega$
	,	I.	ı			<u>'</u>
FRD Forward voltage	V-		1.8		V	I <sub>r</sub> = 30 A <sup>Note3</sup>

Notes: 3. Pulse test.

4. Under development. -The specifications potentially be changed without notice.

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## **Package Dimension**



## **Ordering Information**

Part No.	Quantity	Shipping Container
RJH60D5DPK-00-T0	360 pcs	Box (Tube)

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